

Product Summary

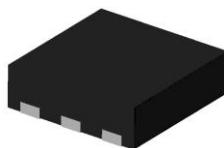
BV_{DSS}	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
30V	20.5m Ω @ $V_{GS} = 10\text{V}$	8.3A
	30m Ω @ $V_{GS} = 4.5\text{V}$	7.4A

Description and Applications

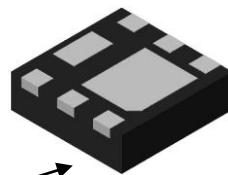
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

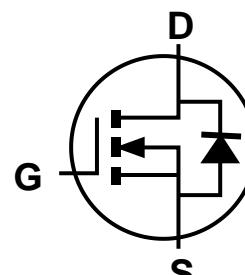
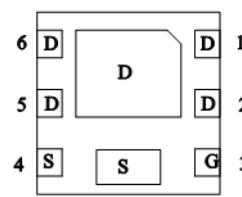
U-DFN2020-6
(Type F)



Top View



Bottom View



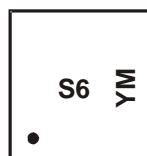
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3025LFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN3025LFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



S6 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: D = 2016)
 M = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023				
Code	D	E	F	G	H	I	J	K				
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	8.3	A
		$T_A = +70^\circ\text{C}$		6.6	
$t < 10\text{s}$		$T_A = +25^\circ\text{C}$	I_D	9.9	A
		$T_A = +70^\circ\text{C}$		7.9	
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	3	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	40	A
Avalanche Current (L = 0.1mH) (Note 7)			I_{AS}	15	A
Avalanche Energy (L = 0.1mH) (Note 7)			E_{AS}	11	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$		P_D	0.66	W
	$T_A = +70^\circ\text{C}$			0.42	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		$R_{\theta JA}$	173	$^\circ\text{C}/\text{W}$
	$t < 10\text{s}$			133	
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$		P_D	2.1	W
	$T_A = +70^\circ\text{C}$			1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		$R_{\theta JA}$	62	$^\circ\text{C}/\text{W}$
	$t < 10\text{s}$			43	
Thermal Resistance, Junction to Case (Note 6)	Steady State		$R_{\theta JC}$	9.4	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}			-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	-	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	-	20.5	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 7\text{A}$
		-	-	30		$V_{GS} = 4.5\text{V}, I_D = 7\text{A}$
Diode Forward Voltage	V_{SD}	-	0.70	1.0	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	641	-	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	66	-		
Reverse Transfer Capacitance	C_{rss}	-	50	-		
Gate Resistance	R_g	-	2.2	-	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	-	6	-	nC	$V_{DS} = 15\text{V}, I_D = 10\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	-	13.2	-		
Gate-Source Charge	Q_{gs}	-	1.7	-		
Gate-Drain Charge	Q_{gd}	-	2.2	-		
Turn-On Delay Time	$t_{D(ON)}$	-	3.3	-	ns	$V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_G = 6\Omega, I_D = 1\text{A}$
Turn-On Rise Time	t_R	-	4.4	-		
Turn-Off Delay Time	$t_{D(OFF)}$	-	22.3	-		
Turn-Off Fall Time	t_F	-	5.3	-		
Reverse Recovery Time	t_{RR}	-	11.4	-	ns	$I_F = 11\text{A}, dI/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	-	8.2	-	nC	$I_F = 11\text{A}, dI/dt = 100\text{A}/\mu\text{s}$

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

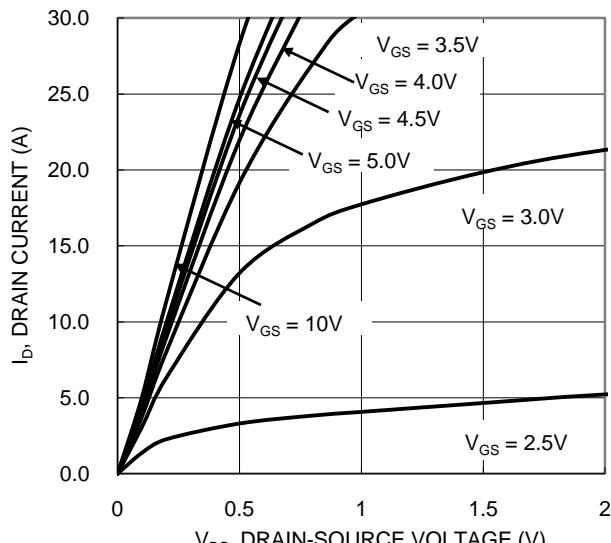


Figure 1. Typical Output Characteristic

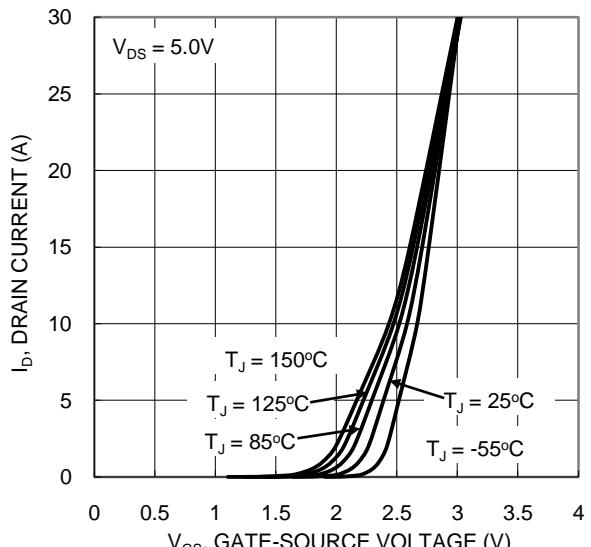


Figure 2. Typical Transfer Characteristic

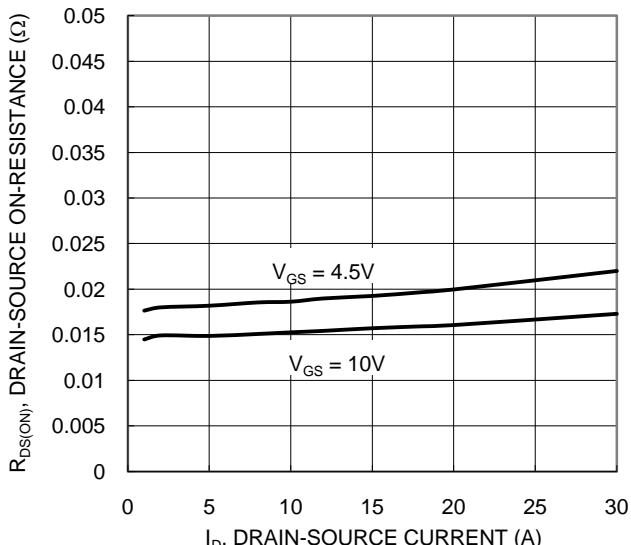


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

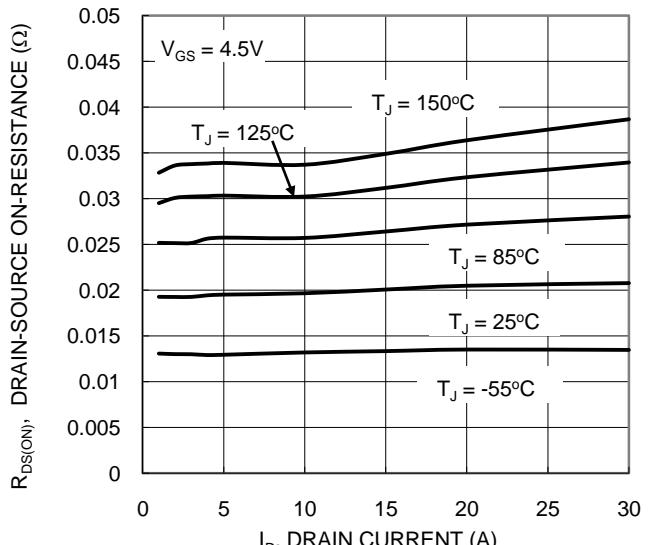


Figure 4. Typical On-Resistance vs Drain Current and Temperature

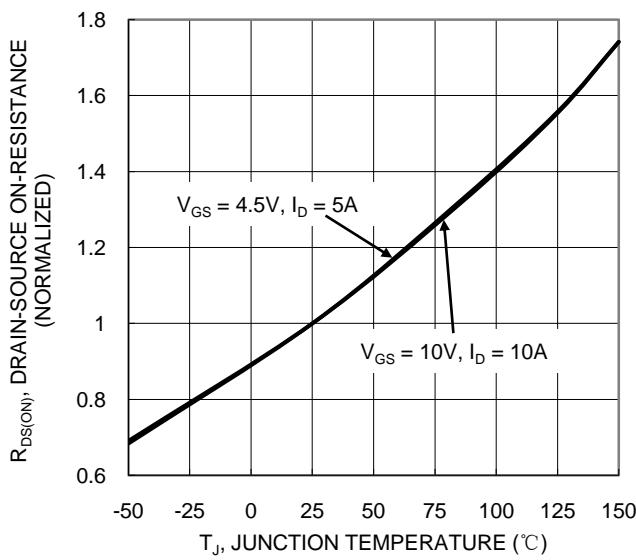


Figure 5. On-Resistance Variation with Temperature

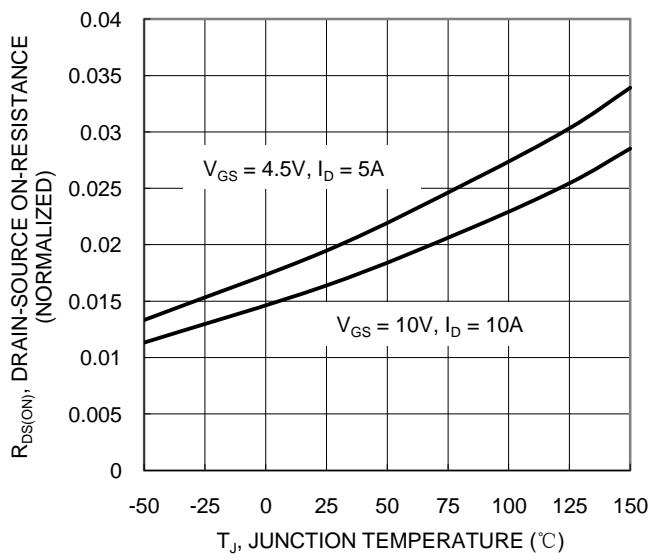
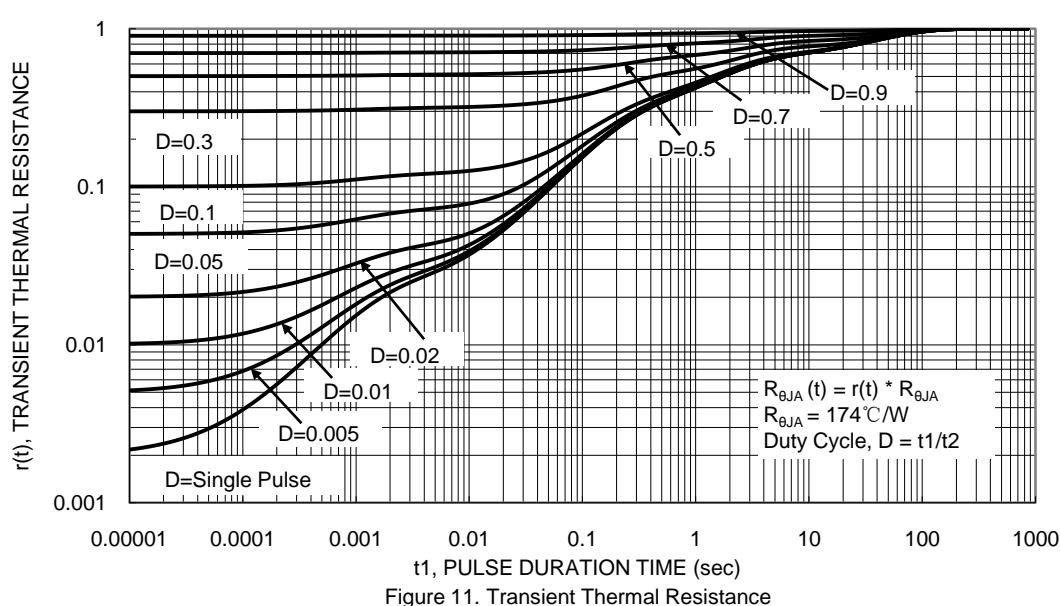
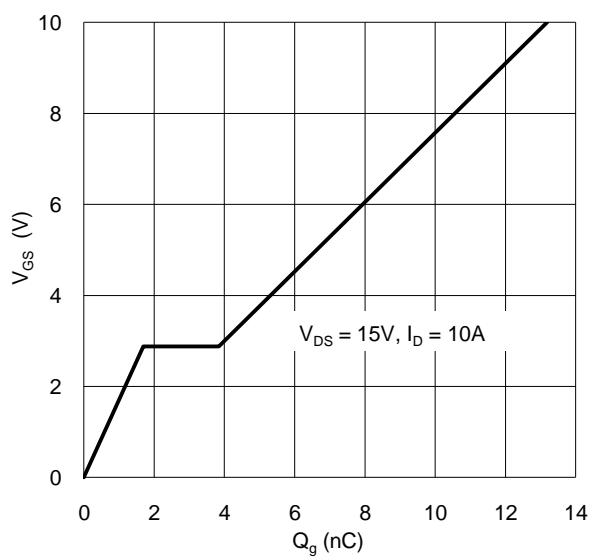
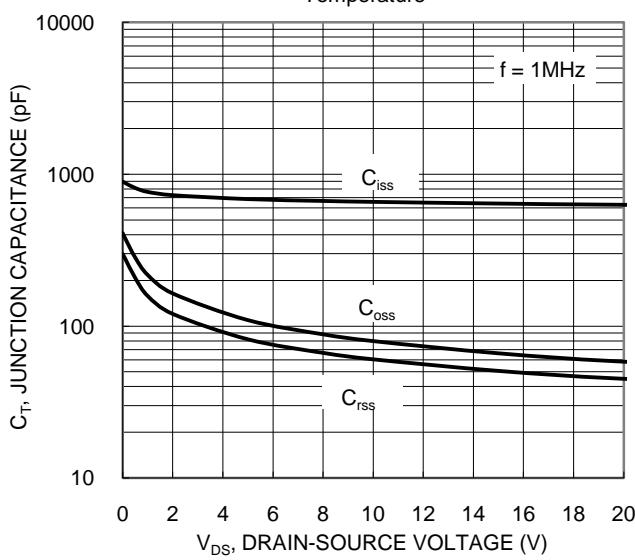
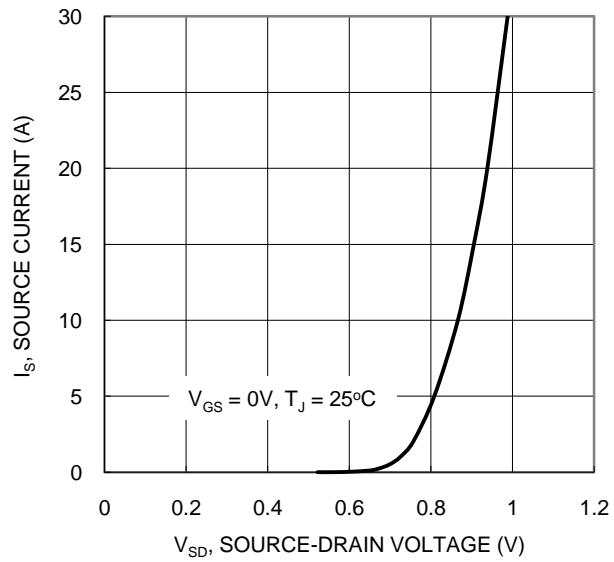
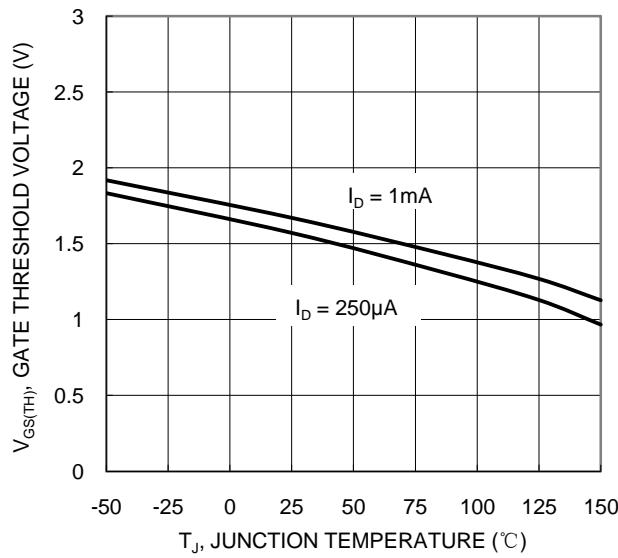


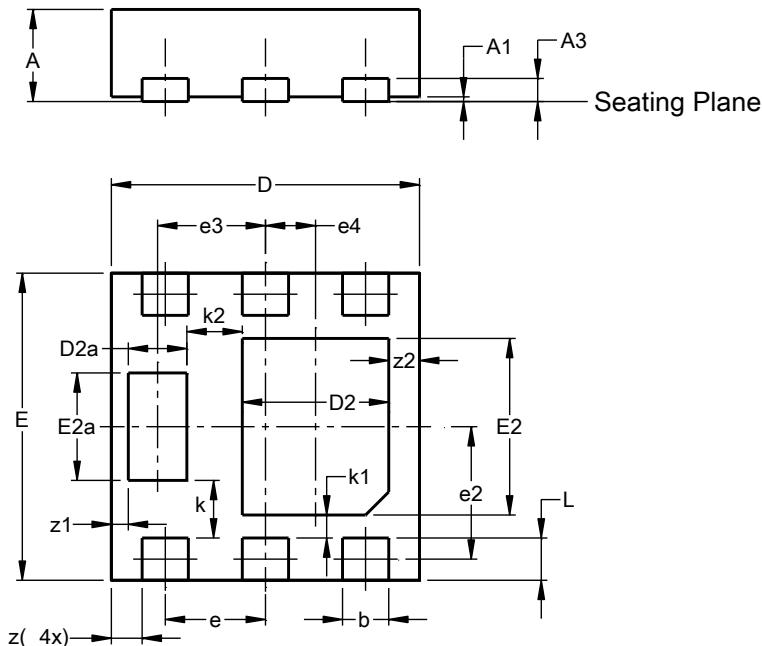
Figure 6. On-Resistance Variation with Temperature



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



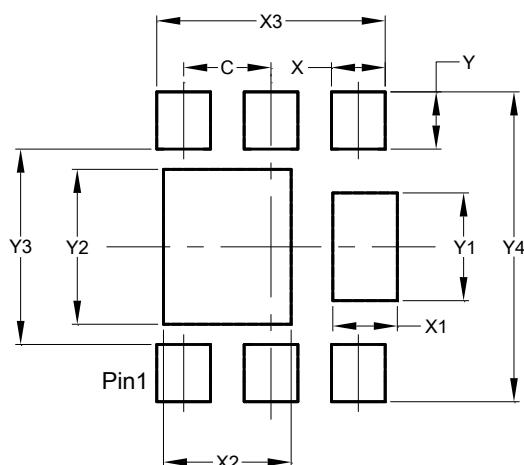
U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65	BSC	
e2	0.863	BSC	
e3	0.70	BSC	
e4	0.325	BSC	
k	0.37	BSC	
k1	0.15	BSC	
k2	0.36	BSC	
L	0.225	0.325	0.275
z	0.20	BSC	
z1	0.110	BSC	
z2	0.20	BSC	

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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